WHAT IS CLAIMED IS:

| 1 | 1. A method for processing integrated circuit devices including a water | | |
|---|---|--|--|
| 2 | recycling process, the process comprising: | | |
| 3 | operating a chemical mechanical planarization process, the chemical mechanical | | |
| 4 | planarization process including a discharge for process water, the process water being used to | | |
| 5 | process one or more semiconductor wafers; | | |
| 6 | selectively discharging process water from the discharge; | | |
| 7 | transferring the process water from the chemical mechanical planarization proces | | |
| 8 | to a facility process; and | | |
| 9 | using the discharged water in the facility process. | | |
| 1 | 2. The method of claim 1 wherein the facility process includes a cooling | | |
| 2 | tower, a local scrubber. | | |
| 1 | 3. The method of claim 1 wherein the discharge water is characterized by a | | |
| 2 | pH value ranging from about 6 to about 10. | | |
| 1 | 4. The method of claim 1 wherein the discharge water is characterized by a | | |
| 2 | conductivity is less than about 2000 μ siemens per centimeter. | | |
| 1 | 5. The method of claim 1 wherein the selectively discharging is provided | | |
| 2 | using a control valve coupled to the discharge, the control valve being coupled to computer | | |
| 3 | hardware. | | |
| 1 | 6. The method of claim 1 wherein the discharge includes a plurality of lines. | | |
| 2 | each of the lines being coupled to one or more processing stations. | | |
| 1 | 7. The method of claim 1 wherein the transferring to the facility process | | |
| 2 | comprises transferring to a collection tank before transferring the discharge water to the facility | | |
| 3 | process. | | |

| 1 | 8. The method of claim 1 wherein the selectively discharging comprises | | | |
|----|---|--|--|--|
| 2 | outputting a signal in response to process in computer software to open a value to release the | | | |
| 3 | process water. | | | |
| 1 | 9. The method of claim 1 wherein the process water is ultra-pure water | | | |
| 2 | having a resistivity of about 18 Mega-ohms. | | | |
| 1 | 10. The method of claim 1 wherein the transferring of the process water from | | | |
| 2 | the chemical mechanical planarization process to a facility process occurs free from any | | | |
| 3 | chemical treatment between the chemical mechanical planarization process and the facility | | | |
| 4 | process. | | | |
| 1 | 11. A method for processing integrated circuit devices including a water | | | |
| 2 | recycling process, the process comprising: | | | |
| 3 | operating a chemical mechanical polishing process using an incoming stream of | | | |
| 4 | ultra-pure water, the chemical mechanical polishing process including a discharge for used ultra | | | |
| 5 | pure water, the ultra-pure water being used to process one or more semiconductor wafers and | | | |
| 6 | discharged through the discharge to form a facility water; | | | |
| 7 | selectively discharging the facility water from the discharge of the chemical | | | |
| 8 | mechanical polishing process and transferring the facility water from the discharge of the | | | |
| 9 | chemical mechanical polishing process to a facility process, the transferring being free from any | | | |
| 10 | chemical treatment of the discharged process water; and | | | |
| 11 | using the discharged water in the facility process. | | | |
| 1 | 12. The method of claim 11 wherein selectively discharging is provided by a | | | |
| 2 | valve coupled to the chemical mechanical planarization process. | | | |
| 1 | 13. The method of claim 11 wherein the ultra-pure water is characterized by a | | | |
| 2 | resistance of about 18 mega-ohm. | | | |
| 1 | 14. The method of claim 13 wherein the ultra-pure water is substantially free | | | |

from particles greater than about 0.05 microns in dimension.

| 1 | 15. | The method of claim 11 wherein the transferring the facility water from | |
|---|--|---|--|
| 2 | the discharge of th | e chemical mechanical polishing process to a facility process includes storing | |
| 3 | the facility water i | n a storage facility before use by the facility process. | |
| | | | |
| 1 | 16. | The method of claim 15 wherein the facility process is selected from a | |
| 2 | cooling process, a scrubbing process. | | |
| 1 | 17. | A system for chemical mechanical polishing, the system comprising: | |
| 2 | ар | lurality of processing stations, each of the processing stations being configured | |
| 3 | to perform at least one processing operation; | | |
| 4 | - | ischarge line coupled to one or more of the processing stations to receive | |
| 5 | discharge water; | | |
| | • | alve coupled to the discharge line to selectively output the discharge water for | |
| 6 | | - | |
| 7 | use in a facility pr | | |
| 8 | a d | rain line coupled to the discharge line for outputting the discharge water to a | |
| 9 | drain. | | |
| 1 | 18. | The system of claim 17 further comprising a computer system coupled to | |
| 2 | the valve, the com | puter system including one or more memories, the one or more memories | |
| 3 | including a first code directed to actuate the value to output the discharge water for use in the | | |
| 4 | facility process. | • | |
| • | ruomity process. | | |
| 1 | 19. | The system of claim 17 wherein the discharge line comprises a plurality of | |
| 2 | lines. | | |
| 1 | 20. | The system of claim 17 further comprising a source line for ultra-pure | |
| 2 | | one or more of the processing stations, the ultra-pure water being discharge | |
| _ | muter coupling to one or more or ma processing summers, and the coupling to one or more or make the coupling to one or more or make the coupling to one or more or make the coupling to one or more or more or more or make the coupling to one or more or mor | | |

water after being used by one or more of the processing stations.